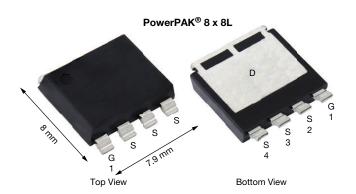


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Vishay Siliconix

# Automotive P-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY				
V <sub>DS</sub> (V)	-40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.0020			
I <sub>D</sub> (A)	-390			
Configuration	Single			
Package	PowerPAK 8 x 8L			

#### **FEATURES**

- AEC-Q101 qualified
- 100 % R<sub>g</sub> and UIS tested
- Thin 1.6 mm package
- · Very low thermal resistance
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



G <b>o</b> —	\$
D 01	B
P-Channel	MOSFFT

<b>ABSOLUTE MAXIMUM RATINGS</b>	<b>S</b> (T <sub>C</sub> = 25 °C, unles	s otherwise noted	1)		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage	V <sub>DS</sub>	-40	V		
Gate-source voltage	$V_{GS}$	± 20			
Continuous drain current	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	-390		
	T <sub>C</sub> = 125 °C		-226		
Continuous source current (diode conduction	I <sub>S</sub>	545	Α		
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	-489		
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	66		
Single pulse avalanche energy	L = 0.1 IIII	E <sub>AS</sub>	218	mJ	
Maximum power dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	600	W	
	T <sub>C</sub> = 125 °C		200	VV	
Operating junction and storage temperature range  Soldering recommendations (peak temperature) <sup>d</sup>		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
			260		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount c	$R_{thJA}$	44	°C/W	
Junction-to-case (drain)		$R_{thJC}$	0.25		

### Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static	•				<u>'</u>	<b>'</b>		
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0$ , $I_D = 250 \mu A$		-40	-	-	V	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$		-2	-2.5		
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	1	-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = -40 V	-	-	1		
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -40 V, T <sub>J</sub> = 125 °C	-	-	200	μA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -40 V, T <sub>J</sub> = 175 °C	1	-	330		
On-state drain current a	I <sub>D(on)</sub>	V <sub>GS</sub> = -10 V	V <sub>DS</sub> ≥ -5 V	-100	-	-	Α	
	, ,	V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = 8 A	-	0.0020	0.0029		
5	_	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -10 A	-	0.0014	0.0020	Ω	
Drain-source on-state resistance a	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -10 A, T <sub>J</sub> = 125 °C	-	-	0.0035		
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = -10 A, T <sub>J</sub> = 175 °C	-	-	0.0040		
Forward transconductance b	9fs	V <sub>DS</sub> =	15 V, I <sub>D</sub> = -50 A	-	180	-	S	
Dynamic <sup>b</sup>		•						
Input capacitance	C <sub>iss</sub>		V <sub>DS</sub> = 25 V, f = 1 MHz	-	44 421	62 190	pF	
Output capacitance	Coss	$V_{GS} = 0 V$		-	1633	2287		
Reverse transfer capacitance	C <sub>rss</sub>			-	1476	2067		
Total gate charge c	$Q_g$			-	487	731	nC	
Gate-source charge c	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = -20 \text{ V}, I_{D} = -30 \text{ A}$	-	89	-		
Gate-drain charge c	$Q_{gd}$			-	82	-		
Gate resistance	R <sub>q</sub>		f = 1 MHz		2.2	3.3	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>				22	33		
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = -20 \text{ V}, \text{ R}_L = 0.67 \Omega$ $I_D \cong -30 \text{ A},  V_{GEN} = -10 \text{ V}, \text{ R}_g = 1 \Omega$		-	30	45	- ns	
Turn-off delay time c	t <sub>d(off)</sub>			-	196	294		
Fall time <sup>c</sup>	t <sub>f</sub>			-	64	96		
Source-Drain Diode Ratings and Cha	racteristics b	1			L	L		
	ta				21	-	ns	
Reverse recovery time	t <sub>b</sub>	V <sub>DD</sub> = -32 V, I <sub>FM</sub> = -20 A, di/dt = 100 A/μs		-	19	-		
•	t <sub>rr</sub>			-	40	80	1	
Reverse recovery charge	Q <sub>rr</sub>			-	42	84	nC	
Reverse recovery current	I <sub>RM</sub>			-	-	2.0	Α	
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	_	1100	Α	
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> = -50 A, V <sub>GS</sub> = 0		_	-0.8	-1.1	V	

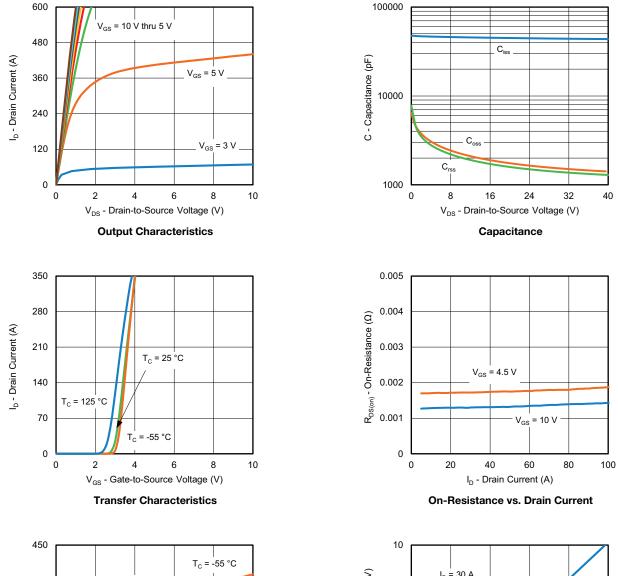
#### Notes

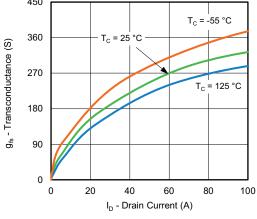
- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

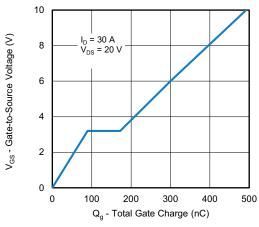


## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)





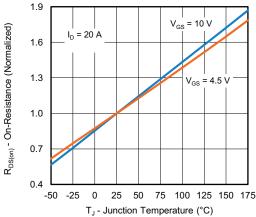
**Transconductance** 



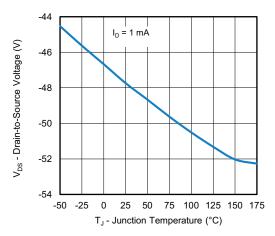
**Gate Charge** 



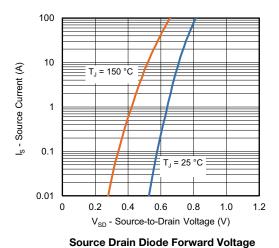
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



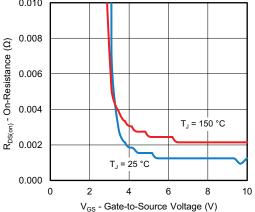
On-Resistance vs. Junction Temperature



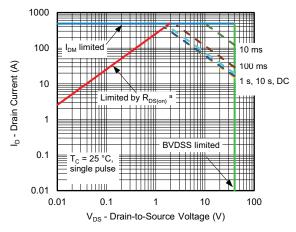
Drain Source Breakdown vs. Junction Temperature



1.9



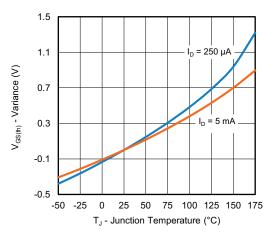
On-Resistance vs. Gate-to-Source Voltage



Safe Operating Area

#### Note

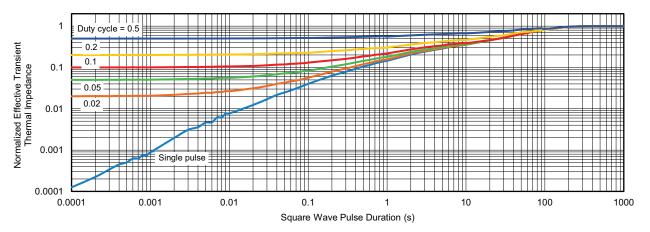
a.  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



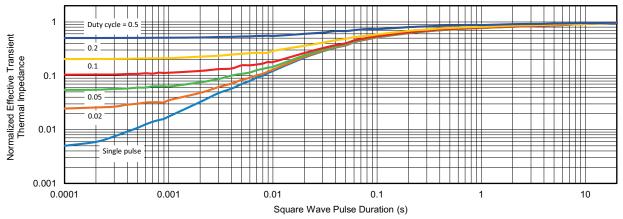
**Threshold Voltage** 



## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?77935">www.vishay.com/ppg?77935</a>.



# PowerPAK® 8 x 8L BWL Case Outline 2



ETERS INCHES		
MAX.		
0.067		
0.005		
0.030		
0.043		
0.046		
0.277		
0.012		
0.315		
0.272		
0.022		
0.106		
0.080		
0.319		
0.249		
0.174		
0.202		
0.157		
0.033		
0.030		
0.045		
0.020		
0.017		
0.026		
0.079		
5°		

ECN: S19-0643-Rev. B, 05-Aug-2019

DWG: 6073

#### Note

Millimeter will govern



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